Inventor: Yongjun Jeff Hu

Title: Methods of Forming Metal Silicide, and Semiconductor

Constructions Comoprising Metal Silicide

Assignee: Micron Technology, Inc.

## <u>INFORMATION DISCLOSURE STATEMENT</u> PURSUANT TO 37 C.F.R. §§ 1.56, 1.97 AND 1.98

In compliance with 37 C.F.R. §§ 1.56, 1.97 and 1.98, the Examiner's attention is directed to the references listed on the attached Form PTO-1449 and copies of which are attached. No admission is made regarding whether all the submitted references are prior art.

Citation of these references is respectfully requested.

Date: June 26, 2003

David G. Latween, Ph.D.

Reg. No. 38,533 Wells, St. John P.S.

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE  LIST OF ART CITED BY APPLICANT  (Use several sheets if necessary)				ATTY. DOCKET NO. M122-2266  APPLICANT Micron Technology, Inc.				SERIAL NO. Filed herewith		
				10		FILING DATE Filed herewith				GROUP		
				U.S. PATENT DOCUMENTS								
*Examiner Initial		Document Number	Date	Name	Name			Class Sub		Filing Date If Appropriate		
	AA	6,187,679	2/13/01	Cabral, Jr. Et al.								
	AB	6,362,086	3/26/02	Weimer et al.								
<del></del>	AC	5,852,319	12/22/98	Kim et al.								
	AD	5,997,634	12/7/99	Sandhu et al.		***						
	AE	6,090,708	7/18/00	Sandhu et al.								
	AF	6,306,766	10/23/01	Sandhu et al.								
AG												
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	AK									Yes	No	
	AL											
	<del></del>		OTHER REFE	RENCES (including Author, Title, Date, l	Perti	nent Pages, Etc.)						
	AM		*Mechanisms for enhanced C54-TiSi <sub>2</sub> formation in Ti-Ta alloy films on single-crystal Si*. A. Quintero et al.; Journal of Materials Research; Vol. 14, No. 12 Dec. 1999 pp. 4690-4700									
	AN	*Enhanced formation of the C54 TiSi <sub>2</sub> by an interposed layer of molybdenum*, A. Mouroux et al.; Appl. Phys. Lett. 69 12 August 1996; ©1996 American Institute of Physics										
	АО	"Low temperature formation of C54-TiSi <sub>2</sub> using titanium alloys", C. Cabral, Jr. Et al; Appl./ Phys. Lett. 71 (24) 15 December 1997 ©1997 American Institute of Physics; pp. 3531-3533										
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		reference considered, whether ext communication to applican		in conformance with MPEP 609; Draw	w lir	ne through citation i	f not in confe	ormano	e and no	ot considered.	Include	